

Title (en)

A single resist layer lift-off process for forming patterned layers on a substrate

Title (de)

Ein-Lagenresist Abhebeverfahren zur Erzeugung eines Musters auf einem Träger

Title (fr)

Procédé de décolage à une seule couche de photorésine pour former des motifs sur un support

Publication

EP 0708372 B1 20000322 (EN)

Application

EP 95305923 A 19950824

Priority

US 32516494 A 19941021

Abstract (en)

[origin: US5654128A] A single resist layer lift-off process for forming patterned layers on a substrate, wherein a post-soak bake is used to control the extent to which chlorobenzene penetrates the resist layer. A post-metallization bake can also be employed to improve lift-off of the resist layer. The process of the present invention provides the resist profile with increased overhang length and the sidewalls of the resist profile with a negative slope. Such increased overhang length and negative slope prevent metallization of the sidewalls of the resist, and thus facilitate more rapid removal of the resist during lift-off.

IPC 1-7

G03F 7/16; G03F 7/42; G03F 7/40

IPC 8 full level

G03F 7/16 (2006.01); **G03F 7/26** (2006.01); **G03F 7/40** (2006.01); **G03F 7/42** (2006.01); **H01L 21/027** (2006.01); **H05K 3/02** (2006.01); **H05K 3/06** (2006.01); **H05K 3/14** (2006.01)

CPC (source: EP US)

G03F 7/168 (2013.01 - EP US); **G03F 7/40** (2013.01 - EP US); **G03F 7/422** (2013.01 - EP US); **H05K 3/143** (2013.01 - EP US)

Cited by

DE19646970A1; EP4350444A1; EP4350443A1; US6852464B2; US6849372B2; US6461795B1; US6596469B2

Designated contracting state (EPC)

DE FR GB

DOCDB simple family (publication)

US 5654128 A 19970805; DE 69515788 D1 20000427; DE 69515788 T2 20000907; EP 0708372 A1 19960424; EP 0708372 B1 20000322; JP H08124848 A 19960517

DOCDB simple family (application)

US 60182696 A 19960215; DE 69515788 T 19950824; EP 95305923 A 19950824; JP 25005195 A 19950905